

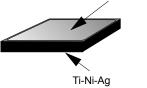


SB060C020-3-W-Ag Schottky cr Barrier Diode Wafer 60 Mils, 20 Volt, 3 Amp, 0.38V_F

Data Sheet

Features

Oxide Passivated Junction Very Low Forward Voltage 125 ° C Junction Operating Low Reverse Leakage Supplied as Wafers Chromium Barrier >1000V ESD (MM) Cr-Al-Ni-Ag - Suffix "Ag"





Electrical Characteristics @ 25°C	Symbol	Unit	SB060C020-3-W-Ag (See ordering code below)
Maximum Repetitive Reverse Voltage (2)	V _{RRM}	Volt	20
Maximum Forward Voltage @ I _F = 3.0A (1)(2)	V _F	Volt	0.38
Typical Average Forward Rectified Current (2)	I _{F(AV)}	Amp	3.0
Reverse Leakage Current @ V_R = 20V (2)	I _{R(1)}	μA	800
Reverse Leakage Current @ V_R =20V, 125°C (2)	I _{R(2)}	mA	50
ESD Machine Model (MM)	V _{ESD(mm)}	Volt	>1000
Junction Operating Temperature Range (2)	TJ	°C	-45 to +125
Storage Temperature Range (2)	T _{SG}	°C	-45 to +125

(1) Pulse Width tp = < 300μ S, Duty Cycle <2%

(2) The characteristics above assume the die are assembled in industry standard packages using appropriate attach methods.

